

# Programmes After Market Services NHM-3 Series Transceivers

## System Module

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## Vocabulary

AFC	Automatic Frequency Control
AGC	Automatic Gain Control
CCONT	Multifunction power management IC for DCT3
CHAPS	Charge Control Switch IC
COBBA_GJP	Mixed signal baseband IC includes RFI and PCM-CODEC, this version further supports PHS and Direct Conversion
CTSI	Control, Timing, Sleep mode and Interrupt module of MAD2WD1. This module takes care of a lot of basic control, e.g. the triggering of events at exact clock tic's as programmed in the registers of the CTSI.
DiCo or DICO	Direct Conversion
ECI	External Control Interface, general interface concept that allows various accessories to be connected independent of the transmission bus. The selection of bus is controlled by the connectivity layer part of the ISA concept.
EEPROM	Electrical Erasable Programmable Read Only Memory
EGSM	Extended GSM, the ordinary GSM band is extended 10 MHz in the low frequency side
FLASH	Re-programmable ROM memory
FPC connector	Flexible printed cable connector
ISA	Intelligent Software Architecture, new modular architecture. The resources are organised in logical groups. These groups are controlled by servers that handles the tasks asked for by the applications. New applications and resources can in a simple way be added to an existing pool
LNA	Low Noise Amplifier, the first stage of the receive chain. The gain may be reduced in one step
MAD2WD1	Version of MAD2PR1 modified for HSCSD & GPRS, same pin out as MAD2PR1
MFI	Module of MAD2WD1 that takes care of communication with the ASIC containing the RF and the Audio AD and DA converters
PA	Power Amplifier
PHS	Personal Handheld System, a digital cordless phone system originated in Japan
RTC	Real Time Clock
SC	System Connector
SIM	Subscriber Identity Module, the intelligent card of the GSM
UIF	User Interface module, a module of the MAD2WD1 that controls the interface to various user interface hardware, e.g. keyboard.
VC(TC)XO	Voltage Control (Temperature Compensated) Crystal Oscillator

## Baseband architecture

The system specific ASIC and the DSP are integrated into one ASIC, called the MAD2WD1. The ARM on the part is able to run at 26MHz, a PLL is included to double the frequency.

Lead megamodule will contain 16KW of RAM and 80KW ROM, (RAM version 112kW for R&D).

Packaged in 144 pin BGA 0.8mm pitch.

The base-band architecture supports a power saving function called "sleep mode", which is 32KHz clock taking over from VCTCXO.

The base-band is running from a 2.8V power rail, which is supplied by a power controlling ASIC (CCONT). In the CCONT ASIC there are 7 individually controlled regulator outputs for RF-section and one 2.8V output for the base-band plus a core voltage for MAD2WD1. In addition there is one +5V power supply output. The CCONT contains also a SIM interface, which supports both 3V and 5V SIM-cards. A real time clock function is integrated into the CCONT, which utilises the same 32kHz clock supply as the sleep clock. The 32KHz clock is generated by the CCONT. A backup power supply is provided for the RTC, which keeps the real time clock running when the main battery is removed. The backup power supply is a rechargeable polyacene battery. The CCONT is supplying the back-up voltage to the RAM from this backup battery. The backup time with this battery is min. ten minutes.

The COBBA\_GJP ASIC provides A/D and D/A conversion of the in-phase and quadrature receive and transmit signal paths and also A/D and D/A conversions of received and transmitted audio signals to and from the UI parts. Data transmission between the COBBA\_GJP and the MAD2WD1 is implemented using serial connections. The COBBA\_GJP ASIC is a triple supply voltage circuit, the digital parts are running from the baseband supply VBB and the analogue parts, both RF and Audio, are running from the analogue supply VCOBBA. COBBA\_GJP supports three external microphone inputs and two external earphone outputs. The inputs can be taken from an internal microphone, a headset microphone or from an external microphone signal source.

Input and output signal source selection and gain control is performed inside the COBBA\_GJP ASIC according to control messages from the MAD2WD1. Keypad tones, DTMF, and other audio tones are generated and encoded by the MAD2WD1 and transmitted to the COBBA\_GJP for decoding.

Digital speech processing is handled by the MAD2WD1 ASIC. MAD2WD1 generates two separate PWM outputs one for a buzzer and one for an internal VIBRA motor.

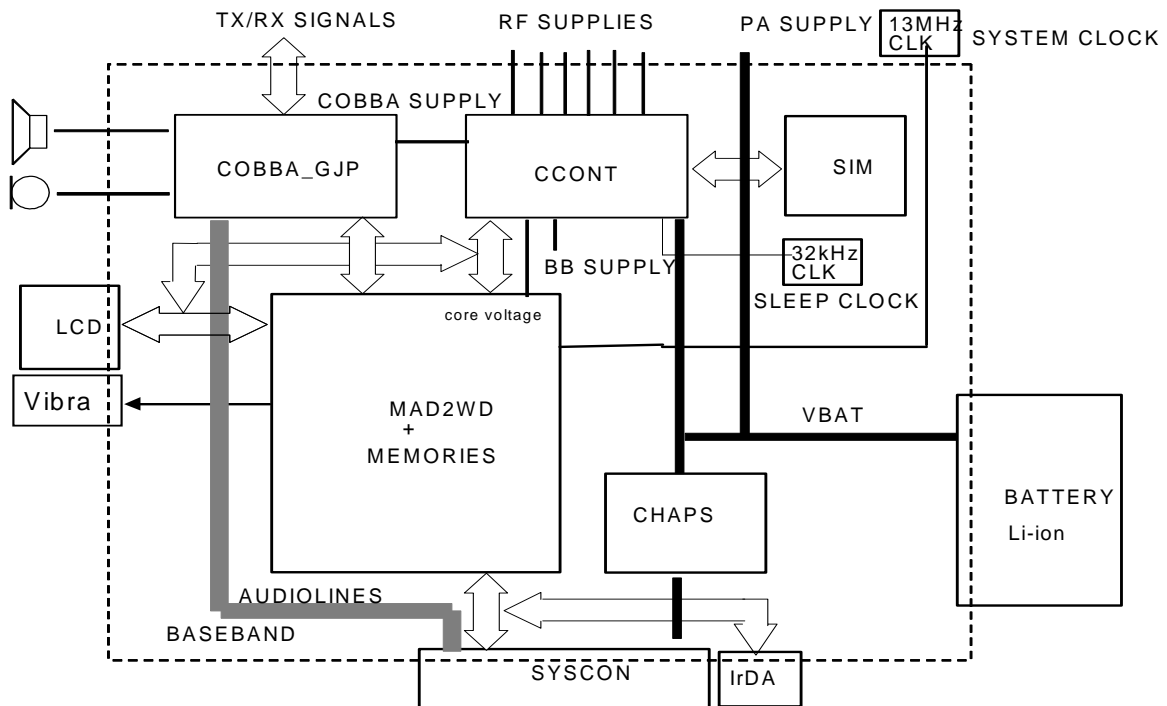


Figure 1: Baseband Block Diagram

The memory configuration is 2Mbit FLASH and 4Mbit RAM, and the EEPROM will be emulated in FLASH. MCUAd21 is externally inverted due the SW demands.

The charger IC, CHAPS will be used in an BGA package, like most of the ASIC's used in this product.

## Audio Parts

Loudspeaker is driven directly by the COBBA.

The Speaker is fixed to the A-cover by a special adapter. Water sealing is handled by a membrane.

Microphone assembly uses in an omnidirectional configuration with open front-hole (membrane sealed). Microphone is connected to COBBA .

The buzzer will be special, NMP code: 5140195. The buzzer is driven by a PWM port through a transistor to allow high current through the coil. It will be made with a spring connector system allowing single side PCB mounting.

The Buzzer is water sealed with a membrane.

**Power Consumption.**

State	Value mA	Note
Stand by, lights off	5	5min average, Sonera SIM
Stand by, lights on	95	
Talk, lights on	390/360	EGSM900/GSM1800, DTX off
Talk, lights off	300/270	EGSM900/GSM1800, DTX off
Talk, lights off	110/130	EGSM900/GSM1800, DTX on

**Vibra power specification**

The Vibra motor is not allowed to draw more current than 128mArms. The maximum voltage across the Vibra must not exceed 2Vrms.

**Electrical Interfaces**

Contains interface descriptions BB-RF & BB-CONN.

**Shielding**

Almost all baseband components must be shielded - the only exceptions are specified below:

- SIM reader. Signals to be ESD/EMI protected.
- System Connector inputs. Signals to be ESD/EMI protected.
- Battery connections. Signals to be ESD/EMI protected.
- IrDA module. Signals to be ESD/EMI protected.
- Keypads. Signals to be ESD/EMI protected.
- LCD module. Signals to be ESD/EMI protected.
- LED's. Signals to be ESD/EMI protected.
- Buzzer Signals to be ESD/EMI protected.
- Speaker. Signals to be ESD/EMI protected.

**System Connector**

The water proof system connector (SC, Code : 5460037) includes the following parts:

DC connector for external plug-in charger and a desktop charger

System connector for accessories and intelligent battery packs excluding the LPRF battery for cordless headset or equivalent. The DLR-3 data cable shall be supported.

Omnidirectional Microphone

Foil for PCB connection, needs also FPC connector

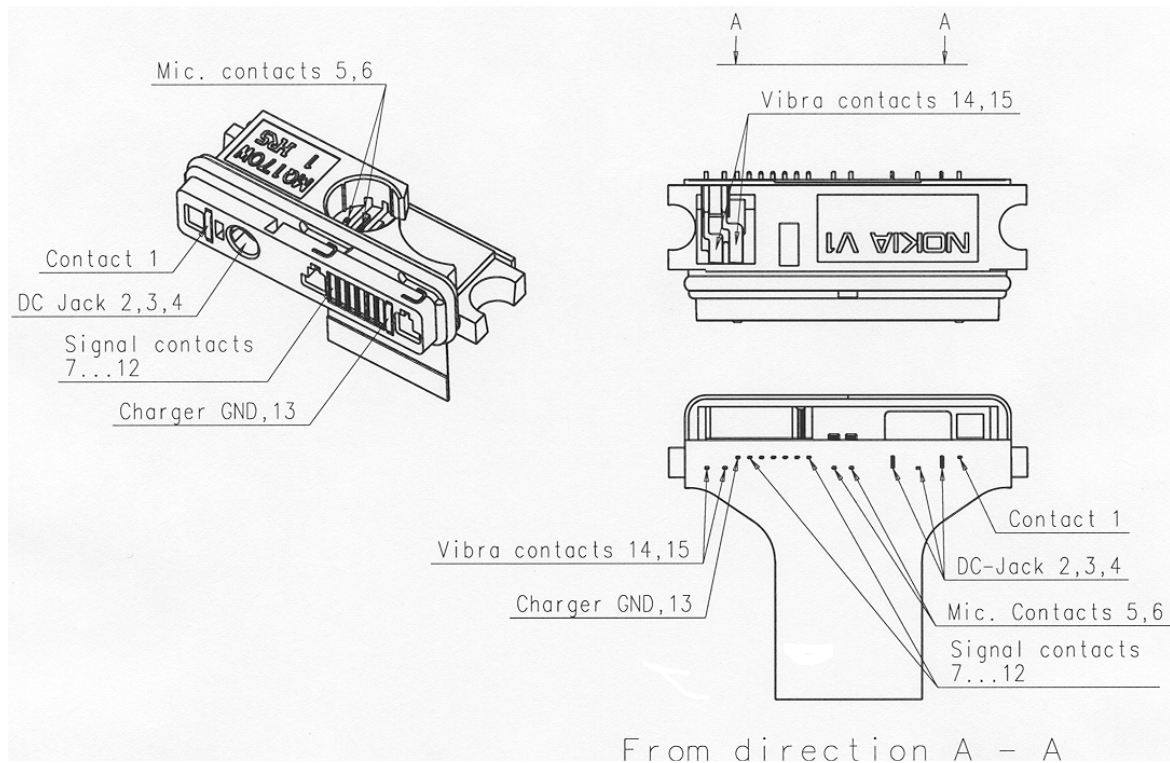


Figure 2: System Connector



Signals of the system connector & FPC connector

FPC pin	SC pin	Name	Min	Typ	Max	Unit	Notes
1 to 4	1	VIN	0		8.5	V	Unloaded Fast Charger
			0		850	mA	Supply current
			0		15.0	Vpeak	Unloaded Standard Charger
					1.0	Apeak	Supply current
5 to 8	2	L_GND	0	0	0	V	Supply ground DC Jack
9 to 12	3	VIN	0		8.5	V	Unloaded Fast Charger DC Jack
			0		850	mA	Supply current
13 to 16	4	CHRG_CTRL	0		0.8	V	Charger control (PWM) <i>dig. Low</i>
			1.7		2.9		DC Jack
							Charger control (PWM) <i>dig. High</i>
							<b>NOTE! This signal is internally connected to phone ground.</b>
17	5	MICP	0	2	100	mV	Connected to COBBA_GJP MIC2P input.
18	6	MICN	0	2	100	mV	Connected to COBBA_GJP MIC2N input.
19	7	XMIC	2.0		2.2	kΩ	Input AC impedance
					1	Vpp	Maximum signal level
			0		1.55	V	Mute (output DC level)
		2.5		2.9	V	Unmute (output DC level)	
		100		600	μA	Bias current	
				200	mVpp	Microphone signal	
						Connected to COBBA_GJP MIC3N + 1N input	
20	8	SGND		330		Ω	Resistance to phone ground, return path for XMIC. When the DLR-3 datacable is connected, SGND switches to be a supply line for the cable (2.8V)
				380		Ω	Resistance to phone ground, return path for XMIC/HMIC. Also used for DLR3 data cable.
21	9	XEAR		47		Ω	Output AC impedance (ref. GND)
				10		μF	Series output capacitance
			16		300	Ω	Load AC impedance to GND (Headset) pin #14
			4.7	10		kΩ	Load AC impedance to GND (Accessory) pin #14
				1.0		Vpp	Maximum output level (no load)

FPC pin	SC pin	Name	Min	Typ	Max	Unit	Notes
				10		k $\Omega$	Load DC resistance to GND (Accessory) pin #14
			16		1500	$\Omega$	Load DC resistance to GND (Headset) pin #14
				2.8		V	DC voltage (47k pull-up to VBB)
		HEAR	0	14	220	mV	Earphone signal Connected to COBBA_GJP HF output
22	10	MBUS	0 2.0		0.8 2.8	V	Serial bidirectional control bus. Baud rate 9600 Bit/s Phone has 4.7k $\Omega$ pull up resistor
23	11	FBUS_RX	0 2.0		0.8 2.8	V	Fbus receive. Serial Data Baud rate 9.6k-230.4kBit/s Phone has 220k $\Omega$ pull down resistor
24	12	FBUS_TX	0.1 1.7		0.8 2.8	V	Fbus transmit. Serial Data Baud rate 9.6k-230.4kBit/s Phone has 47k $\Omega$ pull up resistor
25 to 28	13	L_GND	0		0	V	Supply ground
29	14	VBATIR	3.1		4.2	V	Supply voltage to VIBRA motor (max 200mA)
30	15	VIBRA					GND connection for VIBRA motor (max 200mA)

PCB to foil connection is made by 30-pin FPC connector, NMP code:5469139.

### Interface Base-band to RF

The interface signals between the baseband and the RF section are shown in Table 2 as a logical interface. On the physical board level, baseband supplies voltages from CCONT to the separate RF-sub-blocks. The maximum values specified for the digital signals in the table are the absolute maximum values from the RF interface point of view.

**AC and DC Characteristics of RF/BB signals**

Signal name	From	Parameter	Min	Typ	Max	Unit	Function
1. VBATTRF	BATTERY	Voltage	3.0	3.6	5.1	V	Supply voltage for RF PA
		Current			2500	mA	PA current
2. VREF	CCONT	Voltage	1.478	1.5	1.523	V	1.5V reference.
		Current			100	uA	
		Source resistance		10		ohm	
3. SLE	MAD2WD1 SynthEna	Logic high "1"	2.0		2.8	V	Serial enable, prog PCN/GSM TX/RX and synth.
		Logic low "0"	0		0.5	V	
		Current			50	uA	
		Load capacitance			10	pF	
4. SDATA	MAD2WD1 SyntData	Logic high "1"	2.0		2.8	V	Serial data , prog PCN/GSM TX/RX and synth.
		Logic low "0"	0		0.5	V	
		Load impedance	10			kohm	
		Load capacitance			10	pF	
		Data rate frequency		3.25		MHz	
5. SCLK	MAD2WD1 SynthClk	Logic high "1"	2.0		2.8	V	Serial clk, prog PCN/ GSM TX/RX and synth.
		Logic low "0"	0		0.5	V	
		Load impedance	10			kohm	
		Load capacitance			10	pF	
		Data rate frequency		3.25		MHz	
6. AFC	COBBA_GJP AFCOut	Voltage	0.046		2.254	V	Automatic frequency control signal for VCTCXO

Signal name	From	Parameter	Min	Typ	Max	Unit	Function
		Resolution	11			bits	
		Load resistance (dynamic)	10			kohm	
		Load resistance (static)	1			Mohm	
		Noise voltage			500	$\mu$ Vrms	10...10000Hz
		Settling time			0.5	ms	
7. RFC	VTCX0 To MAD2WD1 (via a divider)	Frequency		13 $\pm$ 1ppm		MHz	High stability clock signal for the logic circuits
		Signal amplitude	0.5	1.0	2.0	Vpp	
		Load resistance	10			kohm	
		Load capacitance	10	12	14	pF	
		Settling time			5	ms	From power on
8/9 . RXI / RXQ	COBBA_GJP	Output level		300	1400	mVpp	Differential RX 13 MHz signal to baseband
	RXIP/RXQP	Source impedance		10		ohm	
		Load resistance		1		Mohm	
		Load capacitance			8	pF	
10.VREF_RX	COBBA_GJP	Voltage		1.2		V	RX signal reference.
	RxRef	Current		100		$\mu$ A	Sink or source
		Source resistance			200		ohm
11/12. TXIP/ TXIN	COBBA_GJP	Differential voltage swing	1.022	1.1	1.18	Vpp	Differential in-phase TX baseband signal for the RF modulator
		DC level	0.784	0.8	0.816	V	
		Differential offset voltage (corrected)			+/- 2.0	mV	

Signal name	From	Parameter	Min	Typ	Max	Unit	Function
		Diff. offset voltage temp. dependence			+/- 1.0	mV	
		Source impedance			200	ohm	
		Load resistance	40			kohm	
		Load capacitance			10	pF	
		DNL			+/- 0.9	LSB	
		INL			+/-1	LSB	
		Group delay mismatch			100	ns	
13/14. TXQP/TXQN	COBBA_GJP	Differential voltage swing	1.022	1.1	1.18	Vpp	Differential quadrature phase TX base-band signal for the RF modulator
		DC level	0.784	0.8	0.816	V	
		Differential offset voltage (corrected)			+/- 2.0	mV	
		Diff. offset voltage temp. dependence			+/- 1.0	mV	
		Source impedance			200	ohm	
		Load resistance	40			kohm	
		Load capacitance			10	pF	
		Resolution	8			bits	
		DNL			+/- 0.9	LSB	
		INL			+/-1	LSB	
		Group delay mismatch			100	ns	
		15. TXP	MAD2WD1	Logic high "1"	2.0		2.8
Logic low "0"	0				0.5	V	
Load Resistance	50					kohm	

Signal name	From	Parameter	Min	Typ	Max	Unit	Function	
		Load Capacitance			10	pF		
		Timing inaccuracy			1	us		
16. TXC	COBBA_GJP TxCOut	Voltage Min	0.12		0.18	V	Transmitter power control	
		Voltage Max	2.27		2.33	V		
		Vout temperature dependence			10	LSB		
		Source impedance active state			200	ohm		
		Source impedance power down state	high Z					
		Input resistance	10			kohm		
		Input capacitance			10	pF		
		Settling time			10	us		
		Noise level			500	uVrms	0...200 kHz	
		Resolution	10			bits		
		DNL			+/-0.9	LSB		
		INL			+/- 4	LSB		
		Timing inaccuracy			1	us		
17. RESET	MAD2WD1	Logic high "1"	2.0		2.8	V	Active low	
		Logic low "0"	0		0.5	V		
		Load Resistance	50			kohm		
		Load Capacitance			10	pF		
		Timing inaccuracy			1	us		

**Power Supplies for RF/BB**

Signal name	From	Parameter	Min	Typ	Max	Unit	Function
1.VXO	CCONT VR1	Voltage Current	2.7	2.8 10	2.85 100	V mA	Vvctcxo
2.VRX_1	CCONT VR2	Voltage Current	2.7	2.8 20	2.85 100	V mA	
3.RAM_BCK	CCONT VR3	Voltage Current	2.7	2.8	2.85 50	V mA	Backup for RAM
4.VSYN_2	CCONT VR4	Voltage Current	2.7	2.8 50	2.85 100	V mA	
5.VSYN_1	CCONT VR5	Voltage Current	2.7	2.8 20	2.85 100	V mA	
6.VCOBBA	CCONT VR6	Voltage Current	2.7	2.8	2.85 100	V mA	VCOBBA
7.VTX	CCONT VR7	Voltage Current	2.7	2.8 70	2.85 150	V mA	Depends on ext. trans (MMBT589LT1)
8.VCP	CCONT V5V	Voltage Current	4.8	5.0	5.2 30	V mA	<b>VSIM and V5V total max 30 mA!</b>
9.VBB	CCONT VBB	Voltage Current	2.7	2.8	2.85 125	V mA	Vbb
10.VIRDA	CCONT VR1_SW	Voltage Current	2.7	2.8	2.85 10	V mA	VlrDA
11.VREF	VREF	Voltage Current	1.478	1.5	1.523 150	V µA	

**Maximum total current from all regulators is 330 mA rms!**

**Serial RF Interface**

The 20pin parallel MAD2--COBBA\_GJ interface is changed to a 5pin serial interface between MAD2WD1 and COBBA\_GJP .

Pin	Width	Purpose
RFclk	1	13MHz Clock to COBBA_GJP
COBBACSX	1	Chip select for general serial interface
COBBASD	1	Serial data for general interface
Idata	1	Bidirectional transfer of I samples 8bit Tx/ 12Bit Rx
Qdata	1	Bidirectional transfer of Q samples 8bit Tx/ 12Bit Rx

## Flash Programming

The Vbb supply on the engine is connected to the programming voltage input of the Flash ROM. This voltage can be used for re-programming in After Sales or in the field. The programming can be made via the buses provided in the bottom and IBI connectors. No external programming voltage source is needed.

In the engine production, the programming voltage is routed via the panel contacts and is "isolated" from the Vbb by means of a resistor or a diode. Thus a higher voltage (e.g.12 V) can be used to speed up the programming in production

### Flash Programming Connections in System Connector

Pin	Name	Parameter	Min	Typ	Max	Unit	Remark
1	VIN	Supply Voltage	6.8	7.8	8.8	V	Supply Voltage
2	GND	GND	0		0	V	Supply ground
10	MBUS	Serial clock from the Prommer	2.0 0		2.8 0.8	V	Prommer detection and Serial Clock for synchronous communication
11	FBUS_RX	Serial data from the Prommer	2.0 0		2.8 0.8	V	Receive Data from Prommer to Baseband
12	FBUS_TX	Data acknowledge to the Prommer	2.0 0		2.8 0.8	V	Transmit Data from Baseband to Prommer
13	GND	GND	0		0	V	Supply ground

### Battery Connector

The electrical specifications for the battery connector (code: 5400163) is shown Table 6. Battery Connector Electrical Specifications . The BSI contact on the battery connector is used to detect when the battery is released from locked position and is going to be removed, in order to be able to shut down the operations of the SIM card before the power is lost, if the battery is removed with power on.

Pin	Name	Min	Typ	Max	Unit	Notes
1	VBAT	3.0	3.6	4.5 5.0 5.3	V	Battery voltage Maximum voltage in call state with charger Maximum voltage in idle state with charger



Pin	Name	Min	Typ	Max	Unit	Notes
2	BSI	0		2.8	V	Battery size indication Phone has 120kohm 1% pull up resistor. SIM Card removal detection (Threshold is 2.4V@VBB=2.8V)
		0		1.0	kΩ	Battery size indication resistor (service battery)
		13		51	kΩ	Battery size indication resistor ()
		62		82	kΩ	Battery voltage indication resistor (Lithium battery) <b>ONLY BLL-2 SUPPORTED!</b>
		-1		1	%	Indication resistor tolerance (pull-down in battery)
		-1		1	%	Pull-up resistor tolerance (120kΩ in phone)
3	BTEMP	0.1		1.4	V	Battery temperature indication Phone has 100kΩ ±1% pull-up resistor, Battery package has NTC pull down resistor: @+25C 47k 5%, B=3750K to 4300K
		2.1 0 5	10	3 0.5 20	V V ms	Phone power up by accessory (input) Input low no action Power up pulse width
		1.9 0 90	100	3.0 1.4 200	V V ms	Accessory power up by phone (output) Accessory low input, no action Power up pulse width
		0		1	kΩ	Fast power up (in production) Pull-down in battery
4	GND	0		0	V	Battery ground

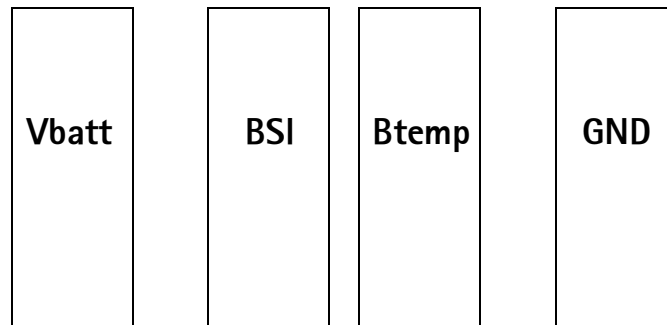


Figure 3: Battery Connector PCB Footprint

### SIM Card Connector : Code 5409145

Only small 3V and 5V SIM cards are supported

Pin	Name	Parameter	Min	Typ	Max	Unit	Notes
1	GND	GND	0		0	V	Ground
2	VSIM	3V SIM Card 5V SIM Card	2.8 4.8	3.0 5.0	3.2 5.2	V	Supply voltage
3	DATA	3V Vin/Vout 5V Vin/Vout	2.8 0 4.0 0		VSIM 0.5 VSIM 0.5	V	Vhigh Vlow SIM data Trise/Tfall max 1us Vhigh Vlow SIM data Trise/Tfall max 1us
4	SIMRST	3V SIM Card 5V SIM Card	2.8 4.0		VSIM VSIM	V	SIM reset
5	SIMCLK	Frequency Trise/Tfall		3.25	25	MHz ns	SIM clock
6	VPP	3V SIM Card 5V SIM Card	2.8 4.8	3.0 5.0	3.2 5.2	V	Programming voltage pin6 and pin2 tied together

VSIM supply voltages are specified to meet type approval requirements regardless of the tolerances of the components used.

### Infrared Interface Module

The module is activated with an VIRDA signal from the CCONT (standby current in shut down mode is specified to 10uA maximum). The RX and TX signals are connected to the MAD2WD1 accessory interface Acclf via FBUS. The Acclf performs pulse encoding and shaping for transmitted data and detection and decoding for received data pulses.

The data is transferred over the IR link using serial FBUS data at speeds 9.6, 19.2, 38.4, 57.6 or 115.2 kbits/. The used IR module complies with the IrDA SIR specification (Infra Red Data Association), which is based on the HP SIR (Hewlett-Packard's Serial Infra Red) concept, IrDA 1.0.

The FBUS cannot be used for "cable" accessory communication when the infrared mode is selected. The infrared communication reserves the FBUS completely.

### Interface Base-band to LCD Module

Based on a Scorpion LCD module with same resolution (96x60 pixels). The driver has the same interface as the Scorpion driver, but the pcb connection is made by foil (12 lines).

Foil Pin	Signal	Symbol	Parameter	Min.	Typ.	Max.	Unit	Notes
1&2			Not Connected					Extra fixing pins
3	VL		Supply voltage	2.7	2.8	3.3	V	
						250	μA	+25 °C, VL=2.85 V,
						250	μA	+25 °C
4	SCLK	f <sub>EXT</sub>	Serial clock input	0		4.00	MHz	
		tscyc		250			ns	
		tshw		100			ns	
		tslw		100			ns	
5	SDA	tsds	Serial data input	100			ns	
		tsdh		100			ns	
6	LCDCDX	tsas	Control/display data flag input	100			ns	Setup time
		tsah		100			ns	Hold time
				LOW				Control data
						HIGH		Display data
7	LCDCSX	tcss	Chip select input	60			ns	
		tcsch		100			ns	
				0.7xVL			V	Logic high
						0.3xVL	V	Logic low, active
8	UDGND	GND	Ground		0		V	In LCD interface
9	VOUT		LCD output voltage			9	V	
10	LCDRSTX		Reset			0.3xVL	V	Logic low, active
		trw		100			ns	for valid reset
11&12			Not Connected					Extra fixing pins

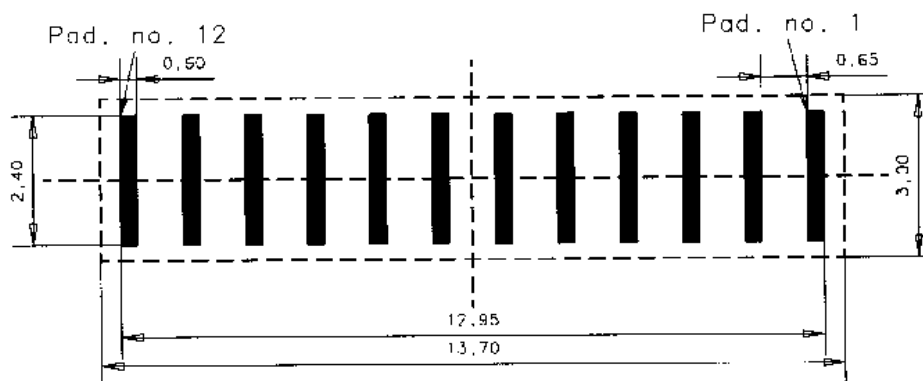


Figure 4: LCD Foil Connection Footprint

### Real Time Clock

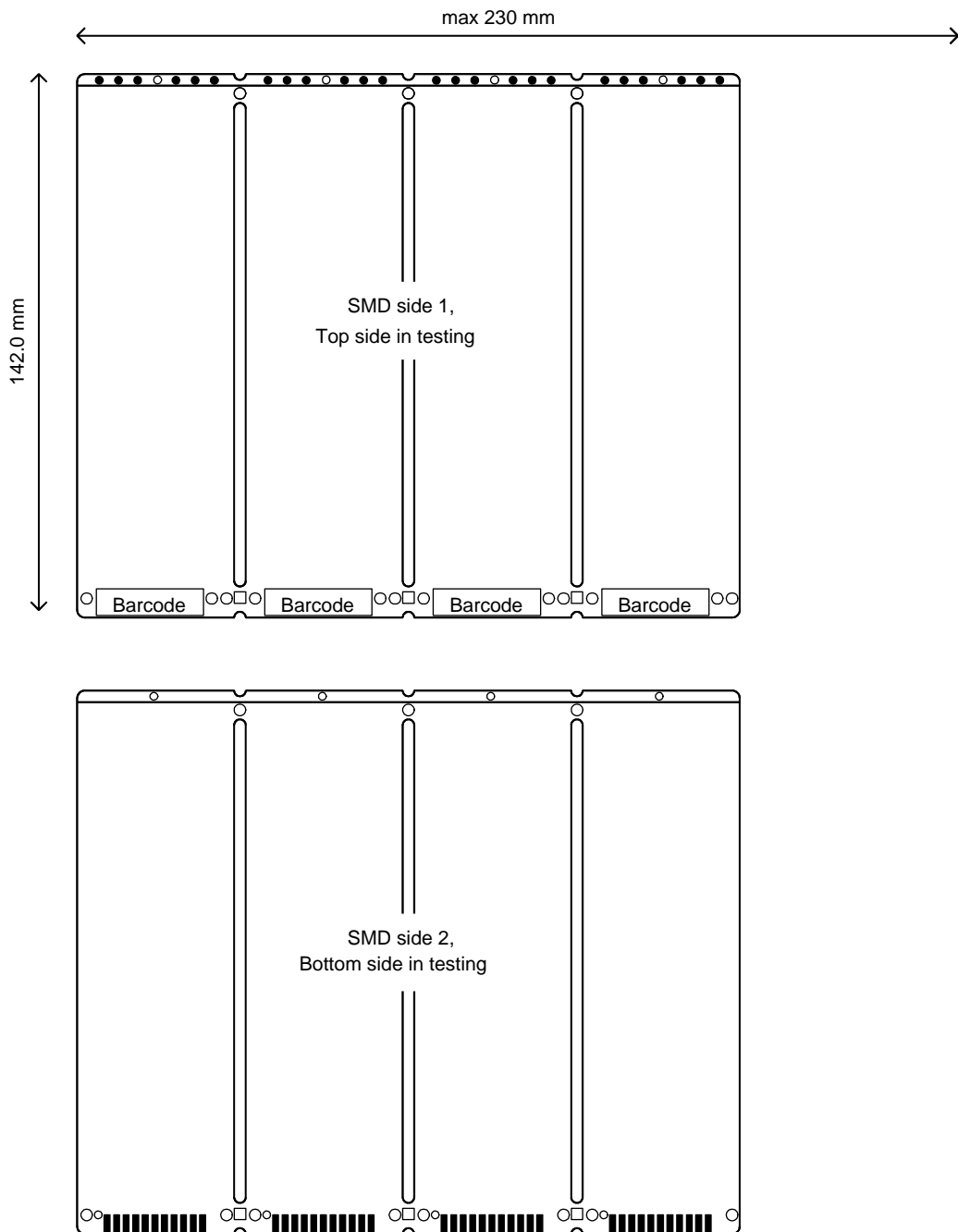
The real time functions in the CCONT are the basic clock and alarm functions, the calendar functions are implemented in MCU software.

### Audio Connections

Pin	Name	Min	Typ	Max	Unit	Remark
n/a	EARN	0	14	220	mV	Connected to COBBA_GJP EARN output. Typical level corresponds to -16 dBm0 network level with volume control giving nominal RLR (=+2dB) 8 db below max. Max level is 0dBm0 with max. volume (codec gain -11 dB)
n/a	EARP	0	14	220	mV	Connected to COBBA_GJP EARP output. Typical level corresponds to -16 dBm0 network level with volume control giving nominal RLR (=+2dB) 8 db below max. Max level is 0dBm0 with max. volume (codec gain -11 dB)
6 on sys. conn.	MICP	0	2	12.5	mV	Connected to COBBA_GJP MIC2P input. The maximum value corresponds to 1 kHz, 0 dBm0 network level with input amplifier gain set to 32 dB. typical value is maximum value - 16 dB.
7 on sys. conn.	MICN	0	2	12.5	mV	Connected to COBBA_GJP MIC2N input. As above.

## Panel Connections

There must be certain signals provided in the engine PCB panel for production functions like tunings and adjustments, Flash programming, etc.



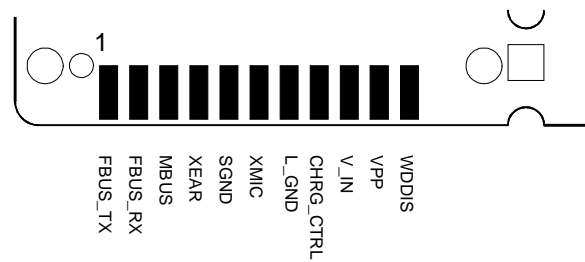


Figure 5: Panel Test Interface Signals

**Production Test Interface**

Pin	Name	Description
1	FBUS_TX	Serial Data Out / Flash Programming Transmit Data.
2	FBUS_RX	Serial Data In / Flash Programming Input Data.
3	MBUS	Bidirectional Serial Bus / Flash Programming Serial Clock.
4	XEAR	Analog Audio Output.
5	SGND	Audio Signal Ground.
6	XMIC	Analog Audio Input.
7	L_GND	Charger Ground.
8	CHRG_CTRL	Charger Control.
9	V_IN	Charging Voltage.
10	VPP	Flash Programming Voltage.
11	WDDIS	Watchdog Disable.

## RF Module

This RF module takes care of all RF functions of EGSM900/GSM1800 dualband engine. RF circuitry is located on one side of the 8-layer transceiver-PCB. PCB area for the RF circuitry is about 15 cm<sup>2</sup>. The RF design is based on the first dualband direct conversion RF-IC "Hagar". So there is no intermediate frequency and that means the number of component is much lower than before and therefore much less interference problems than previously.

EMC emissions are taken care of using metal shielding cans, which screens the whole transceiver. Internal screening is realized by separating different sections of the RF by shielding cans. The VCO is isolated from Hagar and external components by a wall in the Hagar shielding can and PA, RX/TX Switch and LNA's are located in a separate can. The baseband circuitry is located on the same side of the same board, but in a separate shielding can.

## Maximum Ratings

Parameter	Rating
Regulated supply voltage	2.8 +/- 3% V
Voltage reference	1.5 +/- 1.5% V
Operating temperature range	-10...+55 deg. C
Absolute maximum battery voltage	4.2 V (charging)



## RF Characteristics

Item		Values
Receive frequency range	EGSM900	925 ... 960 MHz
	GSM1800	1805 ... 1880 MHz
Transmit frequency range	EGSM900	880 ... 915 MHz
	GSM1800	1710 ... 1785 MHz
Guard Band (RX/TX Spacing)	EGSM900	45 MHz
	GSM1800	95 MHz
Channel spacing	EGSM900	200 kHz
	GSM1800	200 kHz
Number of RF channels	EGSM900	174
	GSM1800	374
Power class	EGSM900	4
	GSM1800	1
Number of power levels	EGSM900	15
	GSM1800	16

In the following it must be observed that requirements specified for the transceiver are taken from the relevant ETSI specifications and is therefore absolute minimum requirements. Margins must be added to the requirements in order to ensure a robust design.

### Internal Antenna

The internal antenna is based on the PIFA concept (Planar Inverted F-Antenna) and is a common design in mobile phone applications. Basically, it is a quarter wave patch which is matched to the required system impedance, typically 50Ω, with a short circuit located at one edge of the patch.

## Internal Antenna Characteristics

Parameter	EGSM900	GSM1800	Unit
Total frequency range	880-960	1710-1880	MHz
Tx frequency range	880-915	1710-1785	MHz
Rx frequency range	925-960	1805-1880	MHz
Nominal impedance	50	50	Ohm
Return loss, free space	>3	>3	dB
Return loss, talk position	>3	>3	dB
Minimum gain	-2	-2	dBd
Power rating (CW, 10 min)	2	2	W

### SAR Performance:

The CENELEC draft recommendation for SAR limits, which the phone in practice has to comply to, is stated below:

$SAR \leq 2.0 \text{ mW/g}$ , averaged over 10 g.

The phone has to be measured in four positions under conditions according to the CENELEC final draft. This applies both to the CENELEC recommendation as well as the internal target at EGSM900 band as well as GSM1800 band.

## RF Frequency Plan

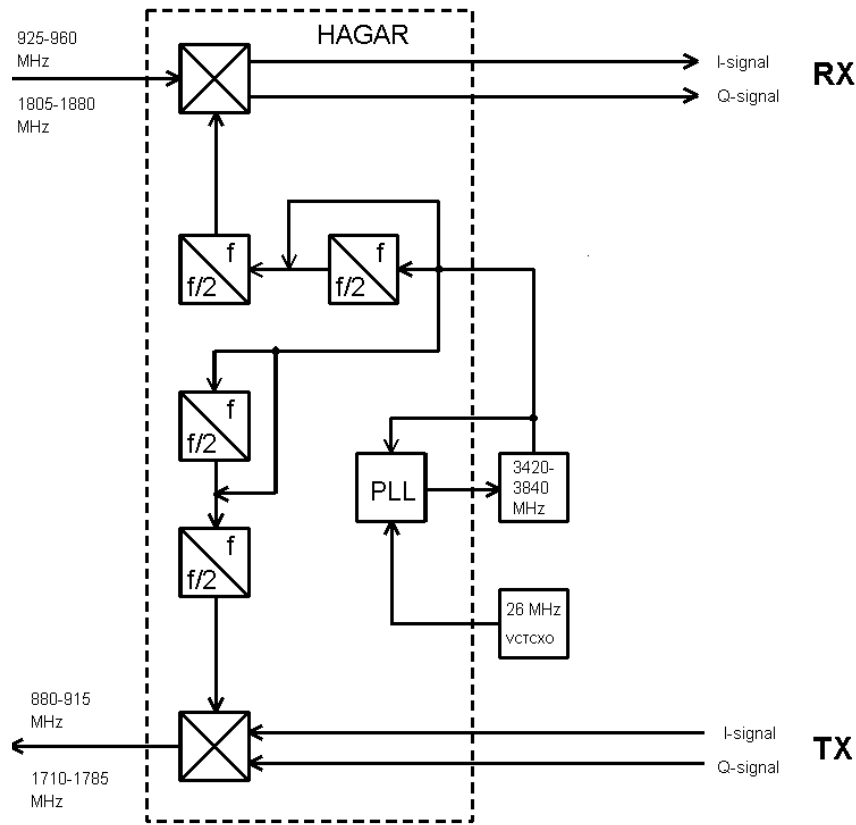


Figure 6: RF Frequency Plan

## DC characteristics

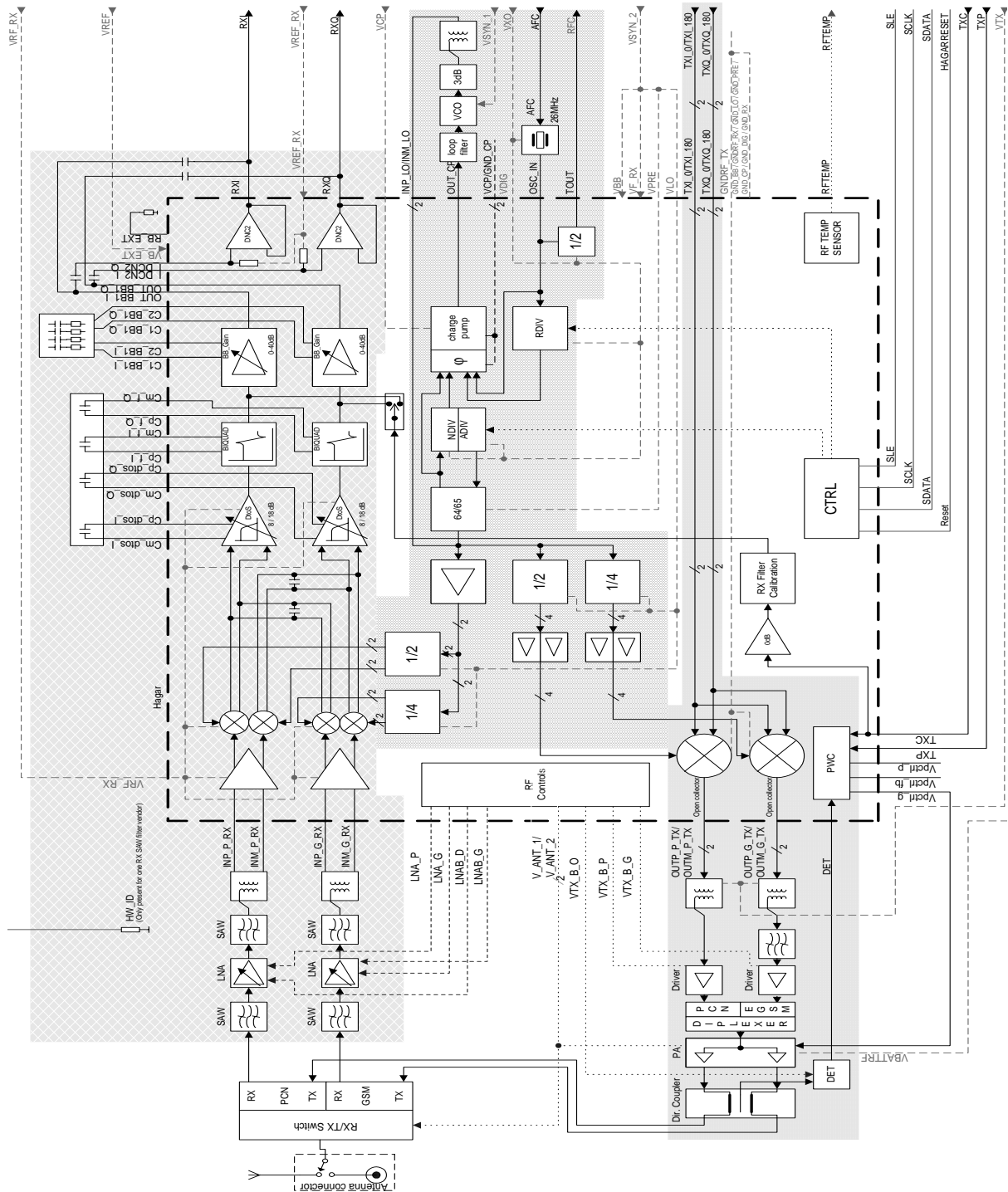
### Regulators

Transceiver has a multi function power management IC at baseband section, which contains among other functions, also 7, 2.8 V regulators. All regulators can be controlled individually with 2.8 V logic directly or through control register. In GSM direct controls are used to get fast switching, because regulators are used to enable RF-functions.

VREF from CCONT IC and VREF RX from COBBA IC are used as the reference voltages for HAGAR RF-IC, VREF (1.5V) for bias reference and VREF RX (1.35V) for RX ADC's reference.

### RF Functional Description-Diagram

Architecture contains one RF-IC, dualband PA module, VCO-module, VCTCXO module and discrete LNA stages for both receive bands.



### Frequency Synthesizer

VCO frequency is locked with PLL into stable frequency source, which is a VCTCXO-module (voltage controlled temperature compensated crystal oscillator). VCTCXO is running at 26 MHz. Temperature effect is controlled with AFC (Automatic Frequency Control) voltage. VCTCXO is locked into frequency of the base station. AFC is generated by baseband with an 11 bit conventional DAC in COBBA.

PLL is located in HAGAR RF-IC and is controlled via serial bus from COBBA-IC (baseband).

There are 64/65 (P/P+1) prescaler, N- and A-divider, reference divider, phase detector and charge pump for the external loop filter. SHF local signal, generated by a VCO-module (VCO = voltage controlled oscillator), is fed to prescaler. Prescaler is a dual modulus divider. Output of the prescaler is fed to N- and A-divider, which produce the input to phase detector. Phase detector compares this signal to reference signal (400kHz), which is divided with reference divider from VCTCXO output. Output of the phase detector is connected into charge pump, which charges or discharges integrator capacitor in the loop filter depending on the phase of the measured frequency compared to reference frequency.

Loop filter filters out the pulses and generates DC control voltage to VCO. Loop filter defines step response of the PLL (settling time) and effects to stability of the loop, that's why integrator capacitor has got a resistor for phase compensation. Other filter components are for sideband rejection. Dividers are controlled via serial bus. SDATA is for data, SCLK is serial clock for the bus and SENA1 is a latch enable, which stores new data into dividers.

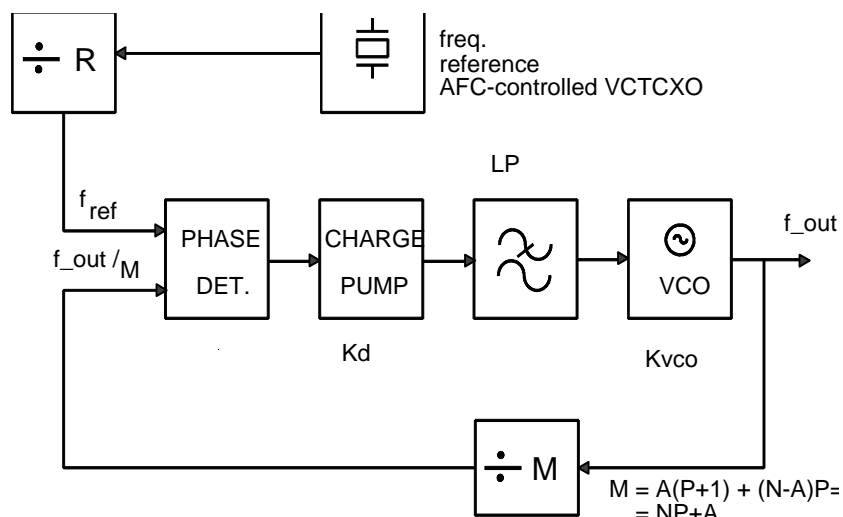


Figure 7: Frequency Synthesiser

LO-signal is generated by SHF VCO module. VCO has double frequency in GSM1800 and 4 frequency in EGSM900 compared to actual RF channel frequency. LO signal is divided by two or four in HAGAR (depending on system mode).

## **AFC function**

AFC is used to lock the transceiver frequency to the frequency of the base station. AFC-voltage is generated in COBBA with 11 bit DA-converter. There is a RC-filter in AFC control line to reduce the noise from the converter. Settling time requirement for the RC-network comes from signaling, how often PSW (pure sine wave) slots occur. They are repeated after 10 frames, meaning that there is PSW in every 46 ms. AFC tracks base station frequency continuously, so transceiver has got a stable frequency, because changes in VCTCXO-output don't occur so fast (temperature).

Settling time requirement comes also from the start up-time allowed. When transceiver is in sleep mode and "wakes" up to receive mode, there is only about 5 ms for the AFC-voltage to settle. When the first burst comes in system clock has to be settled into +/- 0.1 ppm frequency accuracy. The VCTCXO-module requires also 5 ms to settle into final frequency. Amplitude rises into full swing in 1...2 ms, but frequency settling time is higher so this oscillator must be powered up early enough.

## Receiver

The receiver is a direct conversion, dualband linear receiver. Received RF-signal from the antenna is fed via RX/TX switch to 1st RX SAW filter and LNA's (low noise amplifier), separate branches for EGSM900 and GSM1800. Gain selection control of LNA's comes from HAGAR IC. Gain step is activated when RF-level at the antenna (or RF connector) is about -45 dBm.

After the LNA the amplified signal (with low noise level) is fed to bandpass filter (2nd RX SAW filter). RX bandpass filters defines how good suppression of blocking signals outside receive band and the protection against spurious responses.

After the bandpass filters the signals are fed to baluns which converts the single ended signal to balanced. The balanced signal is fed to the RF input of Hagar. Differential RX signal is amplified and mixed directly down to BB frequency in HAGAR. Local signal is generated with external VCO. VCO signal is divided by 2 (GSM1800) or by 4 (EGSM900). PLL and dividers are in HAGAR-IC.

From the mixer output to ADC input RX signal is divided into I- and Q-signals. Accurate phasing is generated in LO dividers. After the mixer DTOS amplifiers convert the differential signals to single ended. DTOS has two gain stages. The first one has constant gain of 12dB and 85kHz cut off frequency. The gain of second stage is controlled with control signal g10. If g10 is high (1) the gain is 6dB and if g10 is low (0) the gain of the stage is -4dB.

The active channel filters in HAGAR provides selectivity for channels (-3dB @ +/-100 kHz typ.). The integrated base band filter is an active-RC-filter with two off-chip capacitors. Large RC-time constants are needed in the channel select filter of the direct conversion receiver. These are produced with large off-chip capacitors. The Baseband filter consists of two stages, DTOS and BIQUAD. The DTOS is a differential to single-ended converter having 8dB or 18dB gain. The BIQUAD is modified Sallen-Key Biquad.

Integrated resistors and capacitors are tunable. These are controlled with a digital control word via Hagar serial interface. The correct control words that compensate for the process variations of integrated resistors and capacitors and of tolerance of off chip capacitors are found during RX filter calibration.

Next stage in the receiver chain is the AGC-amplifier, also integrated into HAGAR. The AGC has digital gain control via serial mode bus from COBBA IC. The AGC-stage provides gain control range (40 dB, 10 dB steps) for the receiver and also the necessary DC compensation. One 10 dB AGC step is implemented in DTOS stages.

DC compensation is made during DCN1 and DCN2 operations (controlled via serial bus). DCN1 is carried out by charging the large external capacitors in the AGC stages to a voltage which cause a zero dc-offset. DCN2 set the signal offset to constant value (VREF RX 1.35 V). The VREF RX signal (from COBBA GJP) is used as a zero level to RX ADCs.

Single ended filtered I/Q-signal is then fed to ADCs in COBBA-IC. Input level for ADC is 1.4 Vpp max.

### **AGC strategy**

AGC-amplifier is used to maintain output level of the receiver in certain range. AGC has to be set before each received burst, to do this pre-monitoring is used to give an estimate of the signal level.

There is 50 dB accurate gain control (10 dB steps) and one larger step (~30 dB) in LNA. LNA AGC step size depends on channel with some amount.

RSSI must be measured accurately on range -48...-110 dBm. At levels higher than -48 dBm the RX level reported by the MS to the base station is always 63.

Production calibration is done with two RF-levels, the LNA gain step is not calibrated.



**Receiver characteristics**

Item	Values
Type	Direct conversion, Linear, DualBand, FDMA/ TDMA
LO frequencies	EGSM900 3700 ... 3840 MHz GSM1800 3610 ... 3760 MHz
Typical 3 dB bandwidth	+/- 104 kHz
Sensitivity	min. - 102 dBm (EGSM900/GSM1800) , S/N >8 dB
Total typical receiver voltage gain ( from antenna to RX ADC )	90 dB
Receiver output level ( RF level -95 dBm )	350 mVpp , single ended I/Q-signals to RX ADCs
Typical AGC dynamic range	80 dB
Accurate AGC control range	50 dB
Typical AGC step in LNA	30 dB
Usable input dynamic range	-102 ... -10 dBm
RSSI dynamic range	-110 ... -48 dBm
Compensated gain variation in receiving band	+/- 1.0 dB

## Transmitter

Transmitter chain consists of final frequency IQ-modulator, dualband power amplifier and a power control loop.

I- and Q-signals are generated by baseband also in COBBA-ASIC. After post filtering (RC-network) they go into IQ-modulator in HAGAR. LO-signal for modulator is generated by VCO and is divided by 2 or by 4 depending on system mode, EGSM900/GSM1800. After modulator the TX-signal is amplified and buffered. There are separate outputs for both EGSM900 and GSM1800. HAGAR TX output level is 5 dBm minimum.

Next TX signals are converted to single ended by discrete baluns. Then TX signals are amplified and buffered in discrete buffers. After the buffers EGSM900 and GSM1800 signals are combined in a diplexer. In EGSM900 branch there is a SAW filter after the balun to attenuate unwanted signals and wideband noise from the Hagar IC.

The final amplification is realized with dualband power amplifier. It has one 50 ohm input and two 50 ohm outputs. There is also a gain control, which is controlled with a power control loop in HAGAR. PA is able to produce over 2 W (3 dBm input level) in EGSM900 band and over 1 W (6 dBm input level) in GSM1800 band into 50 ohm output. Gain control range is over 35 dB to get desired power levels and power ramping up and down.

Harmonics generated by the nonlinear PA are filtered out with the diplexer inside the RX/TX switch-module. Finally the TX signals goes through the RF connector to the internal antenna.

Power control circuit consists of discrete power detector (common for EGSM900 and GSM1800) and error amplifier in HAGAR. There is a directional coupler connected between PA output and RX/TX switch. It is a dualband type and has input and outputs for both systems. Dir. coupler takes a sample from the forward going power with certain ratio. This signal is rectified in a schottky-diode and it produces a DC-signal after filtering.

This detected voltage is compared in the error-amplifier in HAGAR to TXC-voltage, which is generated by DA-converter in COBBA. TXC has got a raised cosine form ( $\cos^4$  - function), which reduces switching transients, when pulsing power up and down. Because dynamic range of the detector is not wide enough to control the power (actually RF output voltage) over the whole range, there is a control named TXP to work under detected levels. Burst is enabled and set to rise with TXP until the output level is high enough, that feedback loop works. Loop controls the output via the control pin in PA to the desired output level and burst has got the waveform of TXC-ramps. Because feedback loops could be unstable, this loop is compensated with a dominating pole. This pole decreases gain on higher frequencies to get phase margins high enough. Power control loop in HAGAR has two outputs, one for each freq. band.

**Transmitter characteristics**

<b>Item</b>	<b>Values</b>
Type	Direct conversion, dualband, non-linear, FDMA/ TDMA
LO frequency range	EGSM900 3520 ... 3660MHz GSM1800 3420 ... 3570 MHz
Output power	2 W / 1 W peak
Gain control range	min. 30 dB
Maximum phase error ( RMS/peak )	max 5 deg./20 deg. Peak

**Parts List of SM4** (EDMS Issue 3.13)

Code:0201490

**ITEM            CODE            DESCRIPTION            VALUE            TYPE**

ITEM	CODE	DESCRIPTION	VALUE	TYPE
R100	1620105	Res network 0w06 2x2k2 j 0404		0404
R101	1825005	Chip varistor vwm14v vc30v 0805		0805
R102	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R103	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R105	1430710	Chip resistor	22	5 % 0.063 W 0402
R106	1419003	Chip resistor	0.22	5 % 1210
R110	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R111	1430826	Chip resistor	680 k	5 % 0.063 W 0402
R112	1430830	Chip resistor	1.0 M	5 % 0.063 W 0402
R113	1430830	Chip resistor	1.0 M	5 % 0.063 W 0402
R120	1430869	Chip resistor	120 k	1 % 0.063 W 0402
R121	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R122	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R123	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R124	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R127	1430830	Chip resistor	1.0 M	5 % 0.063 W 0402
R128	1430826	Chip resistor	680 k	5 % 0.063 W 0402
R160	1620017	Res network 0w06 2x100r j 0404		0404
R172	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R201	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R203	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R206	1620031	Res network 0w06 2x1k0 j 0404		0404
R210	1430718	Chip resistor	47	5 % 0.063 W 0402
R211	1430812	Chip resistor	220 k	5 % 0.063 W 0402
R212	1430762	Chip resistor	2.2 k	5 % 0.063 W 0402
R213	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R214	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R220	1430758	Chip resistor	1.5 k	5 % 0.063 W 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
R221	1430758	Chip resistor	1.5 k	5 % 0.063 W 0402
R222	1430740	Chip resistor	330	5 % 0.063 W 0402
R223	1825021	Chip varistor vwm14v vc46v 0402		0402
R224	1825021	Chip varistor vwm14v vc46v 0402		0402
R226	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R227	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R228	1430780	Chip resistor	12 k	5 % 0.063 W 0402
R233	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R240	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R241	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R245	1430700	Chip resistor	10	5 % 0.063 W 0402
R246	1430700	Chip resistor	10	5 % 0.063 W 0402
R247	1620103	Res network 0w06 2x22r j 0404		0404
R300	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R301	1430726	Chip resistor	100	5 % 0.063 W 0402
R305	1430796	Chip resistor	47 k	5 % 0.063 W 0402
R306	1430812	Chip resistor	220 k	5 % 0.063 W 0402
R370	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R371	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R380	1430693	Chip resistor	5.6	5 % 0.063 W 0402
R381	1430693	Chip resistor	5.6	5 % 0.063 W 0402
R382	1430693	Chip resistor	5.6	5 % 0.063 W 0402
R383	1430693	Chip resistor	5.6	5 % 0.063 W 0402
R401	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R410	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R420	1430718	Chip resistor	47	5 % 0.063 W 0402
R421	1430718	Chip resistor	47	5 % 0.063 W 0402
R422	1430718	Chip resistor	47	5 % 0.063 W 0402
R423	1430718	Chip resistor	47	5 % 0.063 W 0402
R424	1430740	Chip resistor	330	5 % 0.063 W 0402
R425	1430730	Chip resistor	150	5 % 0.063 W 0402
R426	1430738	Chip resistor	270	5 % 0.063 W 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
R427	1430756	Chip resistor	1.2 k	5 % 0.063 W 0402
R430	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R440	1411275	Chip resistor	3.9	5 % 0.2 W 1206
R444	1430770	Chip resistor	4.7 k	5 % 0.063 W 0402
R501	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R502	1430764	Chip resistor	3.3 k	5 % 0.063 W 0402
R503	1430804	Chip resistor	100 k	5 % 0.063 W 0402
R508	1620003	Res network 0w03 4x100r j 0804		0804
R509	1620019	Res network 0w06 2x10k j 0404		0404
R510	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R511	1430846	Chip resistor	2.7 k	1 % 0.063 W 0402
R512	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R513	1620033	Res network 0w06 2x5k6 j 0404		0404
R514	1430848	Chip resistor	12 k	1 % 0.063 W 0402
R515	1430861	Chip resistor	110 k	1 % 0.063 W 0402
R516	1620033	Res network 0w06 2x5k6 j 0404		0404
R517	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R518	1430758	Chip resistor	1.5 k	5 % 0.063 W 0402
R600	1430762	Chip resistor	2.2 k	5 % 0.063 W 0402
R601	1430766	Chip resistor	3.9 k	5 % 0.063 W 0402
R603	1430718	Chip resistor	47	5 % 0.063 W 0402
R604	1430788	Chip resistor	22 k	5 % 0.063 W 0402
R605	1430762	Chip resistor	2.2 k	5 % 0.063 W 0402
R606	1430812	Chip resistor	220 k	5 % 0.063 W 0402
R607	1430740	Chip resistor	330	5 % 0.063 W 0402
R608	1620507	Res network 0w04		3DB ATT 0400404
R611	1430700	Chip resistor	10	5 % 0.063 W 0402
R700	1430718	Chip resistor	47	5 % 0.063 W 0402
R701	1430732	Chip resistor	180	5 % 0.063 W 0402
R702	1430700	Chip resistor	10	5 % 0.063 W 0402
R703	1430690	Chip jumper		0402
R704	1430700	Chip resistor	10	5 % 0.063 W 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
R705	1430726	Chip resistor	100	5 % 0.063 W 0402
R706	1430718	Chip resistor	47	5 % 0.063 W 0402
R708	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R709	1430778	Chip resistor	10 k	5 % 0.063 W 0402
R711	1620507	Res network 0w04		3DB ATT 0400404
R800	1430772	Chip resistor	5.6 k	5 % 0.063 W 0402
R801	1430772	Chip resistor	5.6 k	5 % 0.063 W 0402
R802	1430722	Chip resistor	68	5 % 0.063 W 0402
R803	1430722	Chip resistor	68	5 % 0.063 W 0402
R804	1430718	Chip resistor	47	5 % 0.063 W 0402
R805	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R806	1430730	Chip resistor	150	5 % 0.063 W 0402
R807	1430730	Chip resistor	150	5 % 0.063 W 0402
R808	1430732	Chip resistor	180	5 % 0.063 W 0402
R809	1430726	Chip resistor	100	5 % 0.063 W 0402
R810	1430726	Chip resistor	100	5 % 0.063 W 0402
R811	1430726	Chip resistor	100	5 % 0.063 W 0402
R812	1430726	Chip resistor	100	5 % 0.063 W 0402
R813	1430700	Chip resistor	10	5 % 0.063 W 0402
R814	1430738	Chip resistor	270	5 % 0.063 W 0402
R815	1430738	Chip resistor	270	5 % 0.063 W 0402
R816	1430832	Chip resistor	2.7 k	5 % 0.063 W 0402
R817	1430758	Chip resistor	1.5 k	5 % 0.063 W 0402
R818	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R819	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R820	1430714	Chip resistor	33	5 % 0.063 W 0402
R821	1430700	Chip resistor	10	5 % 0.063 W 0402
R822	1430700	Chip resistor	10	5 % 0.063 W 0402
R823	1430754	Chip resistor	1.0 k	5 % 0.063 W 0402
R900	1430830	Chip resistor	1.0 M	5 % 0.063 W 0402
R910	1430728	Chip resistor	120	5 % 0.063 W 0402
R911	1430728	Chip resistor	120	5 % 0.063 W 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
C100	2310784	Ceramic cap.	100 n	10 % 25 V 0805
C101	2310784	Ceramic cap.	100 n	10 % 25 V 0805
C102	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C103	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C104	2312401	Ceramic cap.	1.0 u	10 % 10 V 0805
C105	2610003	Tantalum cap.	10 u	20 % 10 V 3.2x1.6x1.6
C106	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C110	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C111	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C112	2320544	Ceramic cap.	22 p	5 % 50 V 0402
C113	2320520	Ceramic cap.	2.2 p	0.25 % 50 V 0402
C118	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C119	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C120	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C121	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C122	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C123	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C126	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C127	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C133	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C135	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C137	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C139	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C140	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C141	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C142	2320481	Ceramic cap.	5R 1 u	10 % 0603
C144	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C146	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C147	2610003	Tantalum cap.	10 u	20 % 10 V 3.2x1.6x1.6
C149	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C150	2610003	Tantalum cap.	10 u	20 % 10 V 3.2x1.6x1.6
C152	2610031	Tantalum cap.	10 u	20 % 10 V (2610003)A



ITEM	CODE	DESCRIPTION	VALUE	TYPE
C153	2310793	Ceramic cap.	2.2 u	10 % 10 V 0805
C155	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C157	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C160	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C161	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C162	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C163	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C164	2312401	Ceramic cap.	1.0 u	10 % 10 V 0805
C180	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C181	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C182	2611745	Tantalum cap.	150 u	20 % 10 V 7.3x4.3x2.0
C190	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C202	2320481	Ceramic cap.	5R 1 u	10 % 0603
C203	2610003	Tantalum cap.	10 u	20 % 10 V 3.2x1.6x1.6
C211	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C212	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C213	2610003	Tantalum cap.	10 u	20 % 10 V 3.2x1.6x1.6
C214	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C215	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C220	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C221	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C222	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C223	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C224	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C225	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C226	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C227	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C228	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C229	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C230	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C231	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C232	2320546	Ceramic cap.	27 p	5 % 50 V 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
C233	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C234	2320481	Ceramic cap.	5R 1 u	10 % 0603
C236	2610003	Tantalum cap.	10 u	20 % 10 V 3.2x1.6x1.6
C237	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C238	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C240	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C242	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C243	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C244	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C245	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C246	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C247	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C248	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C249	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C250	2320481	Ceramic cap.	5R 1 u	10 % 0603
C252	2320481	Ceramic cap.	5R 1 u	10 % 0603
C254	2320481	Ceramic cap.	5R 1 u	10 % 0603
C256	2320481	Ceramic cap.	5R 1 u	10 % 0603
C302	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C321	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C322	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C323	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C324	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C325	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C326	2320481	Ceramic cap.	5R 1 u	10 % 0603
C327	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C331	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C332	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C333	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C334	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C335	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C340	2320481	Ceramic cap.	5R 1 u	10 % 0603

ITEM	CODE	DESCRIPTION	VALUE	TYPE
C341	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C349	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C350	2320744	Ceramic cap.	1.0 n	10 % 50 V 0402
C370	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C371	2320131	Ceramic cap.	33 n	10 % 16 V 0603
C372	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C373	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C374	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C375	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C381	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C440	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C441	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C443	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C444	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C450	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C451	2310003	Ceramic cap.	470 n	10 % 16 V 0805
C452	2320481	Ceramic cap.	5R 1 u	10 % 0603
C500	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C501	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C502	2320481	Ceramic cap.	5R 1 u	10 % 0603
C504	2320586	Ceramic cap.	1.2 n	5 % 50 V 0402
C506	2320135	Ceramic cap.	150 n	10 % 10 V 0603
C507	2320135	Ceramic cap.	150 n	10 % 10 V 0603
C508	2320135	Ceramic cap.	150 n	10 % 10 V 0603
C509	2320135	Ceramic cap.	150 n	10 % 10 V 0603
C510	2320485	Ceramic cap.	470 p	5 % 50 V 0603
C512	2320485	Ceramic cap.	470 p	5 % 50 V 0603
C513	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C514	2320485	Ceramic cap.	470 p	5 % 50 V 0603
C516	2320485	Ceramic cap.	470 p	5 % 50 V 0603
C518	2320562	Ceramic cap.	120 p	5 % 50 V 0402
C519	2320781	Ceramic cap.	47 n	20 % 16 V 0603

ITEM	CODE	DESCRIPTION	VALUE	TYPE
C520	2320562	Ceramic cap.	120 p	5 % 50 V 0402
C521	2320781	Ceramic cap.	47 n	20 % 16 V 0603
C522	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C523	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C524	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C525	2320552	Ceramic cap.	47 p	5 % 50 V 0402
C526	2320552	Ceramic cap.	47 p	5 % 50 V 0402
C527	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C528	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C529	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C531	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C532	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C600	2320522	Ceramic cap.	2.7 p	0.25 % 50 V 0402
C601	2610031	Tantalum cap.	10 u	20 % 10 V (2610003)A
C602	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C603	2320578	Ceramic cap.	560 p	5 % 50 V 0402
C604	2312217	Ceramic cap.	10 n	5 % 16 V 0805
C605	2320578	Ceramic cap.	560 p	5 % 50 V 0402
C606	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C607	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C608	2312211	Ceramic cap.	3.3 u	10 % 0805
C609	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C611	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C612	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C613	2320552	Ceramic cap.	47 p	5 % 50 V 0402
C614	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C615	2320621	Ceramic cap.	0.5 p	0.25 % 50 V 0402
C700	2320530	Ceramic cap.	5.6 p	0.25 % 50 V 0402
C701	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C702	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C703	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C704	2320783	Ceramic cap.	33 n	10 % 10 V 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
C705	2320552	Ceramic cap.	47 p	5 % 50 V 0402
C707	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C708	2320548	Ceramic cap.	33 p	5 % 50 V 0402
C712	2320520	Ceramic cap.	2.2 p	0.25 % 50 V 0402
C713	2320524	Ceramic cap.	3.3 p	0.25 % 50 V 0402
C714	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C715	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C716	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C717	2320560	Ceramic cap.	100 p	5 % 50 V 0402
C718	2320783	Ceramic cap.	33 n	10 % 10 V 0402
C719	2320592	Ceramic cap.	2.2 n	5 % 50 V 0402
C724	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C725	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C726	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C727	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C800	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C801	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C802	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C803	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C804	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C805	2320522	Ceramic cap.	2.7 p	0.25 % 50 V 0402
C806	2320508	Ceramic cap.	1.0 p	0.25 % 50 V 0402
C807	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C808	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C809	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C810	2320584	Ceramic cap.	1.0 n	5 % 50 V 0402
C811	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C812	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C814	2320620	Ceramic cap.	10 n	5 % 16 V 0402
C815	2611745	Tantalum cap.	150 u	20 % 10 V 7.3x4.3x2.0
C817	2312293	Ceramic cap.		Y5 V 1206
C818	2320546	Ceramic cap.	27 p	5 % 50 V 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
C819	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C820	2320532	Ceramic cap.	6.8 p	0.25 % 50 V 0402
C821	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C822	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C823	2320516	Ceramic cap.	1.5 p	0.25 % 50 V 0402
C824	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C825	2320805	Ceramic cap.	100 n	10 % 10 V 0402
C826	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C828	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C829	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C830	2320516	Ceramic cap.	1.5 p	0.25 % 50 V 0402
C831	2320095	Ceramic cap.	3.3 n	5 % 50 V 0603
C832	2320518	Ceramic cap.	1.8 p	0.25 % 50 V 0402
C910	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C911	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C912	2320546	Ceramic cap.	27 p	5 % 50 V 0402
C913	2320540	Ceramic cap.	15 p	5 % 50 V 0402
C915	2320508	Ceramic cap.	1.0 p	0.25 % 50 V 0402
L101	3203701	Ferrite bead 33r/100mhz 0805		0805
L120	3203701	Ferrite bead 33r/100mhz 0805		0805
L121	3203701	Ferrite bead 33r/100mhz 0805		0805
L122	3203701	Ferrite bead 33r/100mhz 0805		0805
L123	3203701	Ferrite bead 33r/100mhz 0805		0805
L202	3203801	Chip bead array 2x1000r 0405		0405
L204	3203801	Chip bead array 2x1000r 0405		0405
L601	3648808	Chip coil		10 % Q=50 1206
L700	3646059	Chip coil	5 n	Q=28/800M 0402
L701	3646051	Chip coil	3 n	Q=28/800M 0402
L702	3646059	Chip coil	5 n	Q=28/800M 0402
L703	3645185	Chip coil	10 n	5 % Q=12/100 MHz 0603
L704	3645177	Chip coil	27 n	5 % Q=26/800 MHz 0603
L708	3646047	Chip coil	3 n	Q=28/800M 0402

ITEM	CODE	DESCRIPTION	VALUE	TYPE
L800	4551013	Dir.coupl.897.5/1747.5mhz 2.1x1.3		2.1x1.3
L801	3646085	Chip coil	6 n	10 % Q=29/800 MHz 0402
L802	3645163	Chip coil	22 n	10 % Q=12/100 MHz 0603
L804	3645017	Chip coil	5 n	10 % Q=10/100 MHz 0603
L806	3646051	Chip coil	3 n	Q=28/800M 0402
L808	3646051	Chip coil	3 n	Q=28/800M 0402
L811	3646087	Chip coil	1 n	Q=31/800M 0402
L901	3646069	Chip coil	33 n	5 % Q=23/800 MHz 0402
L902	3646069	Chip coil	33 n	5 % Q=23/800 MHz 0402
B110	4510293	Crystal	32.768 k	+ -20PPM 12.5PF
G600	4350261	Vco 3420-3840mhz 2.7v 20ma 9x7		9X7
G602	4510261	VCTCXO	26 M	+ -5PPM 2.7V GSM
F101	5119019	SM, fuse f 1.5a 32v 0603		
Z201	3640035	Filt z>450r/100m 0r7max 0.2a 0603		0603
Z700	4511127	Saw filter	942.5+- 17.5 M	/3.5DB 3X3
Z701	4511129	Saw filter	1842.5+- 37.5 M	
Z702	4511129	Saw filter	1842.5+- 37.5 M	
Z703	4511127	Saw filter	942.5+- 17.5 M	/3.5DB 3X3
Z800	4550067	Dipl 880-960/1710-1880mhz 3.2x2.5		3.2x2.5
Z802	4511095	Saw filter	897.5+- 17.5 M	/3.5DB 3X3
Z900	4512131	Ant.swit 880-960/1710-1880mhz 7x5		7X5
T600	3640423	Transf balun 3.7ghz+/-300mhz 0805		0805
T700	3640405	Transf balun 900mhz+/-100mhz 1210		1210
T701	3640421	Transf balun 1.8ghz+/-100mhz 1206		1206
T800	3640405	Transf balun 900mhz+/-100mhz 1210		1210
T840	3640421	Transf balun 1.8ghz+/-100mhz 1206		1206
V120	4110601	Diode	FAST	SOD323
V140	4210215	Transistor	MMBT589	pnp 30 V 1 A SOT23
V150	4110067	Schottky diode	MBR0520L	20 V 0.5 A SOD123

ITEM	CODE	DESCRIPTION	VALUE	TYPE
V160	4113671	Tvs esda6v1w5 ** no new design **		**
V170	4113611	Emifilt/tvs emif01-10005w5 sot353		SOT353
V171	4113611	Emifilt/tvs emif01-10005w5 sot353		SOT353
V202	4210121	Transistor		SOT323
V210	4113671	Tvs esda6v1w5 ** no new design **		**
V221	4211621	MosFet	2 FDG	SOT363
V231	4210121	Transistor		SOT323
V400	4110601	Diode	FAST	SOD323
V410	4110089	Diode x 2	BAV70W	70 V .5 A 4 ns SOT323
V411	4200836	Transistor	BCX19	nnp 50 V 0.5 A SOT23
V418	4864291	Led	Green	1305
V419	4864291	Led	Green	1305
V420	4864291	Led	Green	1305
V421	4864291	Led	Green	1305
V422	4864291	Led	Green	1305
V423	4864291	Led	Green	1305
V424	4864291	Led	Green	1305
V425	4864291	Led	Green	1305
V426	4864291	Led	Green	1305
V427	4864291	Led	Green	1305
V428	4864291	Led	Green	1305
V429	4864291	Led	Green	1305
V430	4200843	Transistor	BCX18	pnp 25 V 0.5 A SOT23
V431	4200843	Transistor	BCX18	pnp 25 V 0.5 A SOT23
V432	4210100	Transistor	BC848W	nnp 30 V SOT323
V433	4110072	Diode x 2	BAV99W	70 V 0.2 A SOT323
V440	4110089	Diode x 2	BAV70W	70 V .5 A 4 ns SOT323
V441	4200226	Darl. transistor	BCV27	nnp 30 V 300 mA SOT23
V450	4113671	Tvs esda6v1w5 ** no new design **		**
V600	4210100	Transistor	BC848W	nnp 30 V SOT323
V700	4210271	Transistor		SCT598
V701	4210275	Transistor		SCT598



ITEM	CODE	DESCRIPTION	VALUE	TYPE
V800	4110079	Sch. diode x 2	HSMS282C	15 V SOT323
V801	4210183	Transistor	BFP193W	npn 8G V SOT343
V802	4210183	Transistor	BFP193W	npn 8G V SOT343
V803	4117971	Diode	LM4041CI M3-ADJ	SOT23
D100	4340767	IC, MCU	MC33460	
D301	4370687	Mad2wd1 v16 rom6 f741541h ubga144		UBGA144
D302	4340845	1xinverter 1.8v-5.5v(7sz04)sc70-5		
D310	4340787	IC, SRAM		CSP48
D311	4340597	IC, flash mem.		UBGA48
D370	4340369	IC, dual bus buffer sso	TC7W126F U	SSOP8
N100	4370621	Chaps v2.0 u423v20g36t lbga6x6		
N102	4370719	Ccont 2m wfd163mg64t/8 lfbga8x8		
N240	4370643	Cobba_gjp v4.1 v257bg64t/8 bga64		BGA64
N371	4860035	TFDS 4400 IRDA	115.2K2V7	Sideview
N500	4370667	Hagar 3 sttza8hg80t lfbga80		LFPGA80
N501	4340797	IC, regulator	LP2980IM5 X-4.7	4.7 V SOT23-5
N800	4350203	IC, pow.amp.		3.5 V 3.5V
S400	5209001	SM, sw tact spst 12v 50ma side k		KEY
S401	5209001	SM, sw tact spst 12v 50ma side k		KEY
S402	5209001	SM, sw tact spst 12v 50ma side k		KEY
X100	5469139	SM, fpc conn 30pol p0.5 0.4a ver		VERT
X160	5409145	SM, sim conn 2x3pol p2.54 h=1.95		H=1.95MM
X900	5420033	SM, conn rf pcb-part float 1mm		
A001	9517051	RF shield assy dmc02108 hda13		
A002	9510625	Bb shield frame dmd05800-en haral		HARAL
A003	9510629	Pa-shield frame dmd05532 harald		HARALD
	4850151	LCD display module assy dmc02837 haral		HARALD
	9854463	PCB SM4 43.9X122.85X1.0 M8 4/PA		
	9854463	PC board	SM4	43.9x122.85x1.0 m8 4/pa

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